查询MCH6702供应商 捷多邦，专业PCB打样工厂，24小时加急出货

Ordering number : ENN6684A

PNP Epitaxial Planar Silicon Transistor
Schottky Barrier Diode

MCH6702

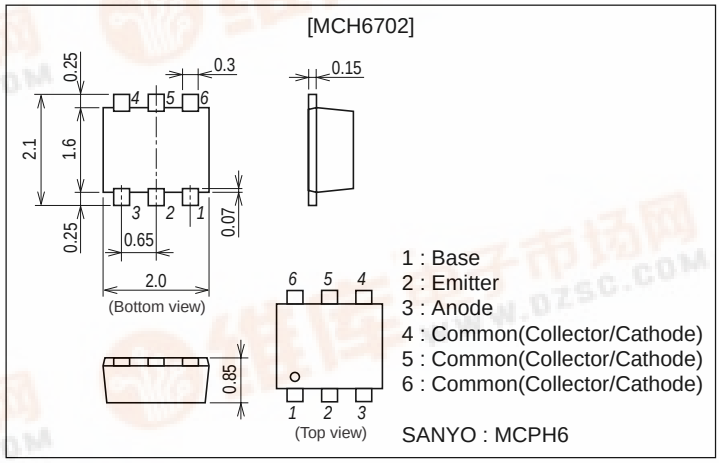
DC/DC Converter Applications

Features

- Composite type with a PNP transistor and a Schottky barrier diode contained in one package facilitatiing high-density mounting.
- The MCH6702 consists of two chips which are equivaient to the MCH6101 and SBS006, respectively.
- The ultrasmall package facilitates miniaturization in end products. (mounting height 0.85mm).

Package Dimensions

unit : mm
2191A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[TR]				
Collector-to-Base Voltage	V_{CBO}		-15	V
Collector-to-Emitter Voltage	V_{CEO}		-15	V
Emitter-to-Base Voltage	V_{EBO}		-5	V
Collector Current	I_C		-1.5	A
Collector Current (Pulse)	I_{CP}		-3	A
Base Current	I_B		-300	mA
Collector Dissipation	P_C	Mounted on a ceramic board(600mm²X0.8mm)	1.0	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	V_{RRM}		30	V
Non-repetitive Peak Reverse Surge Voltage	V_{RSM}		30	V
Average Output Current	I_O		0.7	A
Surge Current	I_{FSM}	50Hz sine wave, 1 cycle	10	A
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

Marking : PB

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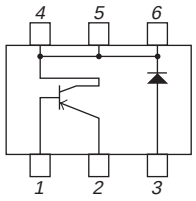
■ SANYO assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO products described or contained herein.

Electrical Characteristics at Ta=25°C

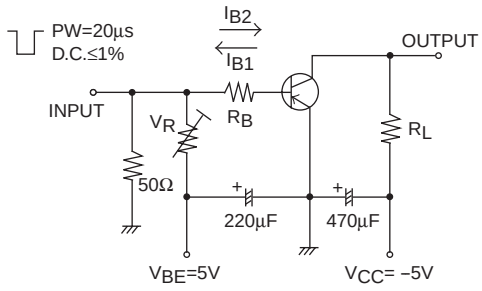
Parameter	Symbol	Conditions	Rathings			Unit
			min	typ	max	
[TR]						
Collector Cutoff Current	I_{CBO}	V_{CB}=-12V, I_E=0			-0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-4V, I_C=0			−0.1	μA
DC Current Gain	h_{FE}	V_{CE}=-2V, I_C=-100mA	200		560	
Gain-Bandwidth Product	f_T	V_{CE}=-2V, I_C=-300mA		350		MHz
Output Capacitance	Cob	V_{CB}=-10V, f=1MHz		17		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=-750mA, I_B=-15mA		−120	−180	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=-750mA, I_B=-15mA		−0.85	−1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-10μA, I_E=0	−15			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, R_{BE}=∞	−15			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	−5			V
Turn-ON Time	t_{on}	See specified Test Circuit		50		ns
Storage Time	t_{stg}	See specified Test Circuit		90		ns
Fall Time	t_f	See specified Test Circuit		15		ns
[Di]						
Reverse Voltage	V_R	I_R=0.5mA	30			V
Forward Voltage	V_F1	I_F=0.3A		0.35	0.40	V
	V_F2	I_F=0.5A		0.42	0.47	V
	V_F3	I_F=0.7A		0.5	0.55	V
Reverse Current	I_R	V_R=10V			200	μA
Interterminal Capacitance	C	V_R=10V, f=1MHz		20		pF
Reverse Recovery Time	t_{rr}	I_F=I_R=100mA, See specified Test Circuit			10	ns

Electrical Connection



Switching Time Test Circuit

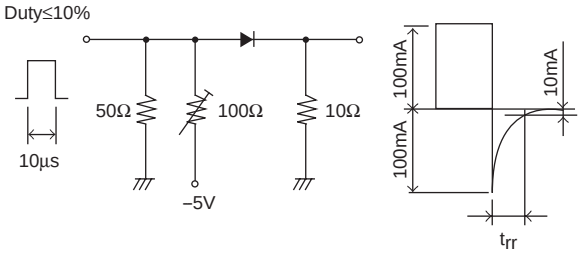
[TR]



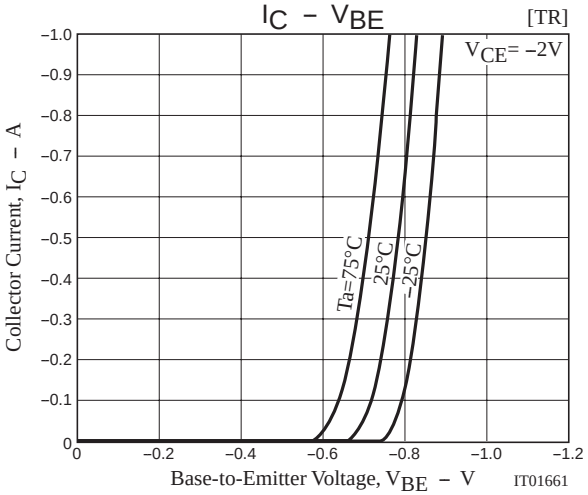
I_C= −20I_{B1}=20I_{B2}= −750mA

t_{rr} Specified Circuit

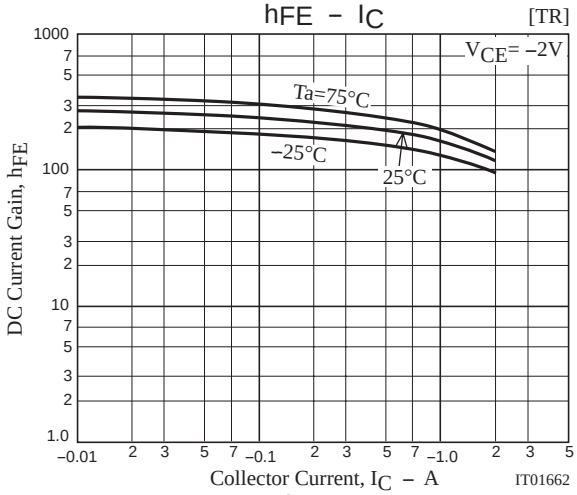
[Di]



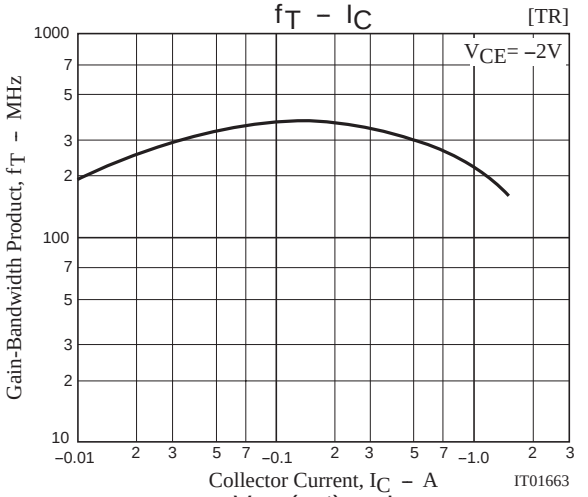
I_C – V_{BE} [TR]



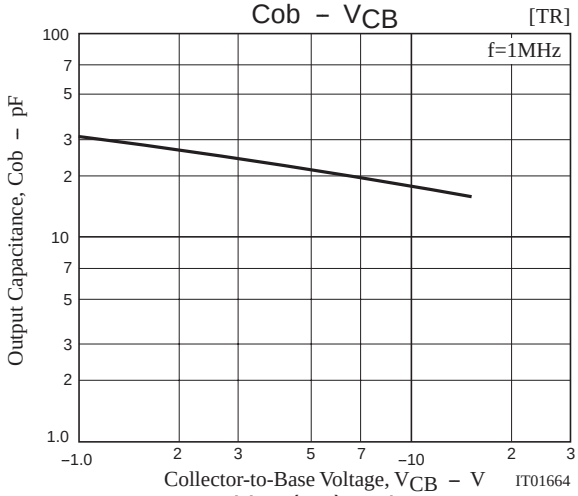
hFE – I_C [TR]



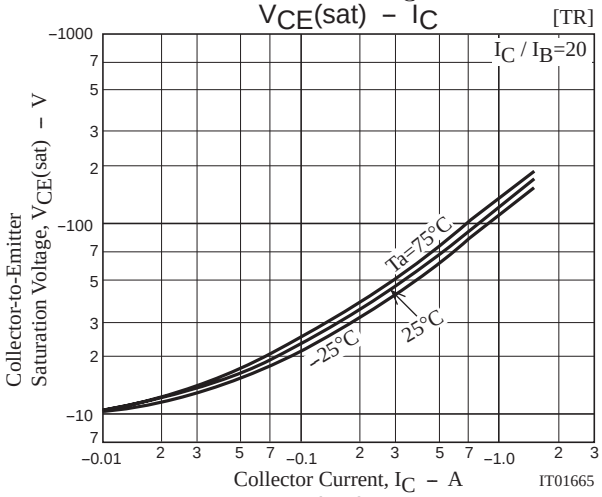
f_T – I_C [TR]



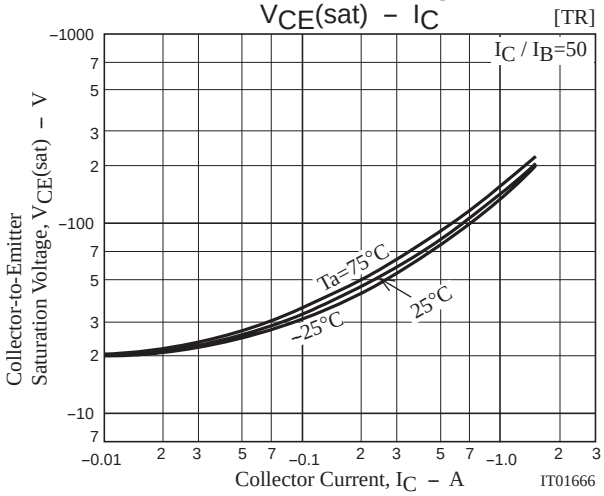
Cob – V_{CB} [TR]



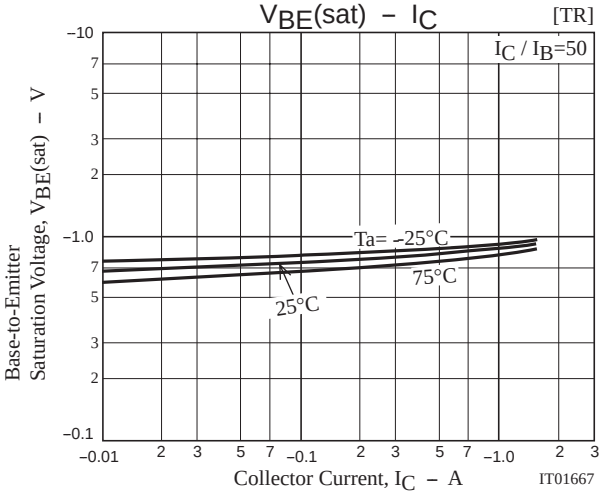
V_{CE}(sat) – I_C [TR]



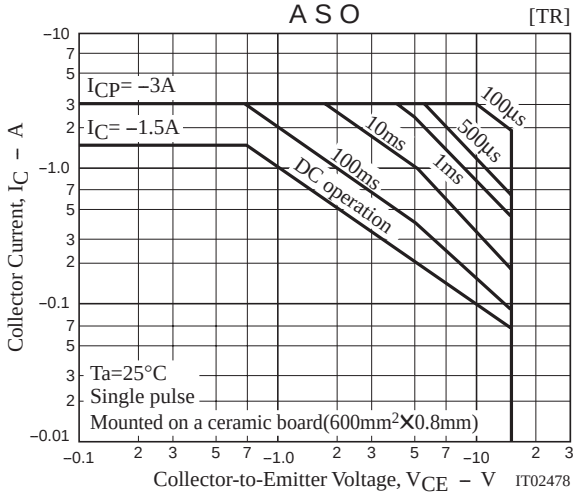
V_{CE}(sat) – I_C [TR]

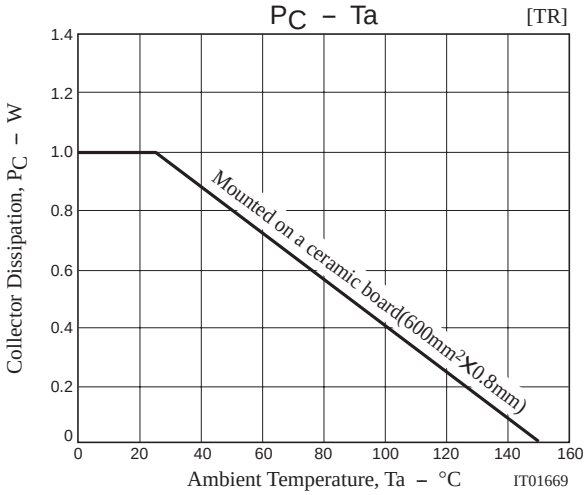


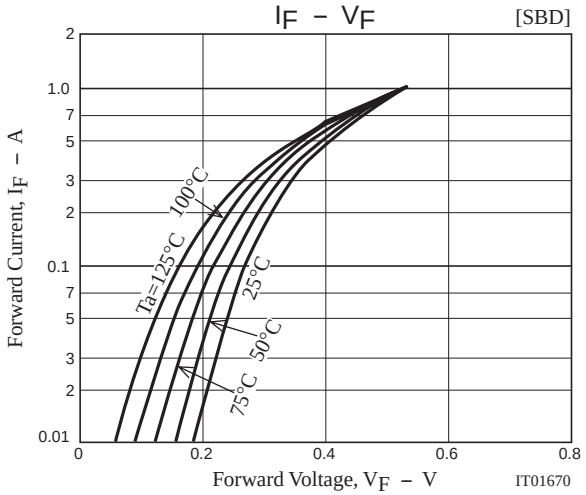
V_{BE}(sat) – I_C [TR]

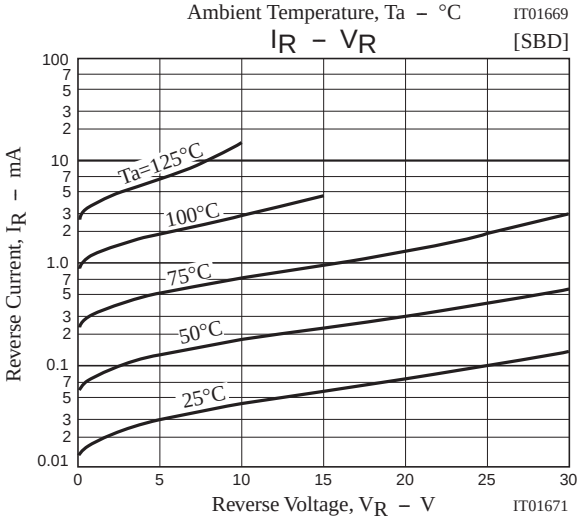


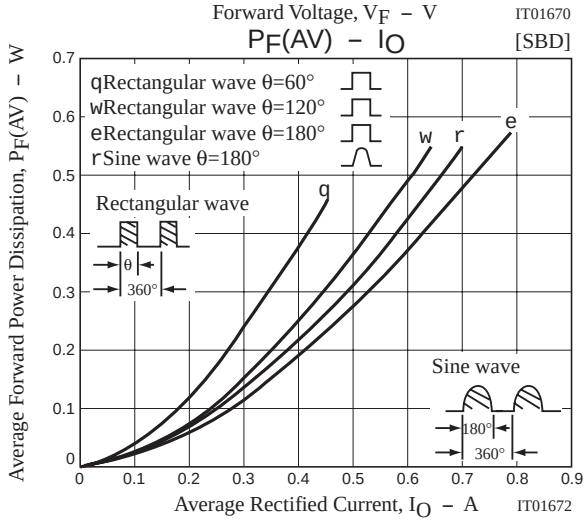
A S O [TR]











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